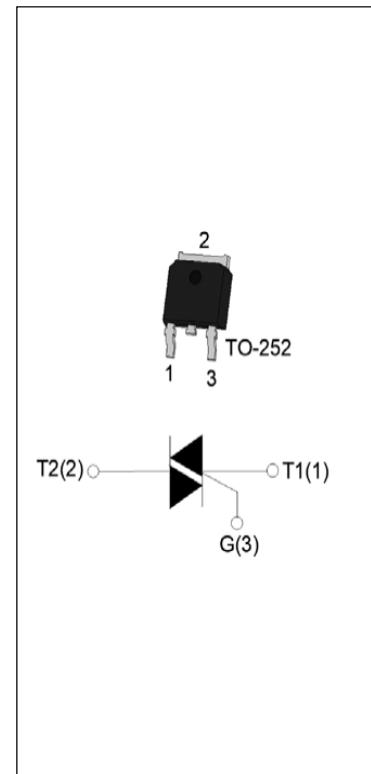


BTB08D-800SW
MAIN FEATURES 3Q TRIAC

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM}/V_{RRM}	800	V
$I_{GT1/2/3}$	10/10/10	mA

DESCRIPTION:

The BTB08D-800SW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. BTB08D-800SW snubberless triac is especially recommended for use on inductive loads. It can be driven directly through the MCU I/O port. Package TO-252 is RoHS compliant.


ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c \leq 90^\circ\text{C}$)	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle, $t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	80	A
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	64	A^2s
Critical rate of rise of on-state current ($T_j=125^\circ\text{C}$)	di/dt	50	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	1	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V}$ $R_L=100\Omega$	I - II -III	MAX.	10	mA
V_{GT}		I - II -III	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=100\Omega$	I - II -III	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III	MAX.	60	mA
		II		100	
I_H	$I_T=500\text{mA}$		MAX.	60	mA
dV/dt	$V_D=2/3V_{DRM}$ $T_j=125^\circ\text{C}$		MIN.	500	V/ μs
$(dI/dt)_c$	$T_j=125^\circ\text{C}$		MIN.	10	A/ms

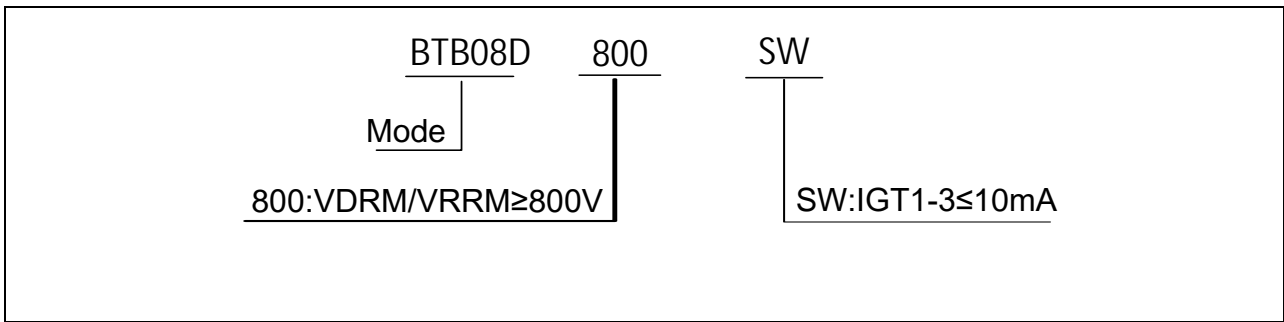
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=32\text{A}$	$T_j=25^\circ\text{C}$	1.5	V
V_{TO}	Threshold voltage	$T_j=125^\circ\text{C}$	0.86	V
R_D	Dynamic resistance	$T_j=125^\circ\text{C}$	36.6	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	μA
I_{RRM}		$T_j=125^\circ\text{C}$	1	mA

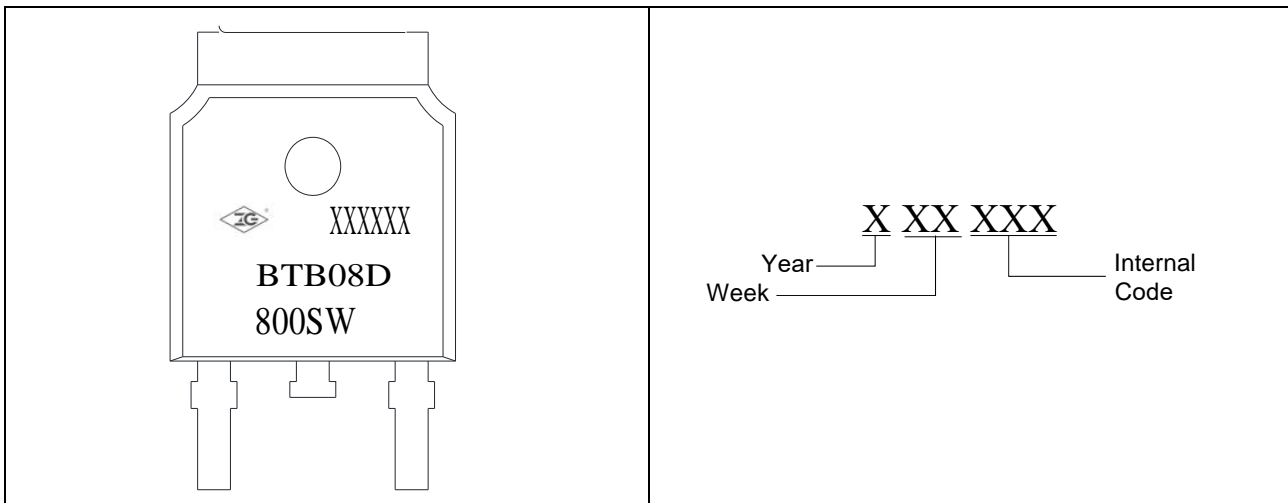
THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.25	$^\circ\text{C}/\text{W}$

ORDERING INFORMATION



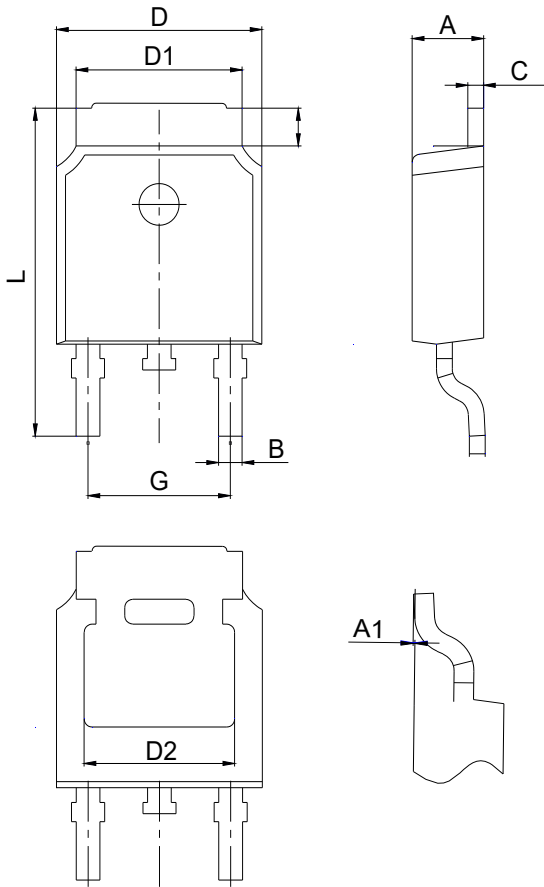
MARKING



ORDERING INFORMATION

Order code	Voltage V _{DRM} /V _{R_{RRM}} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I -II-III			
BTB08D-800SW	800	10	TO-252	2500	Tube

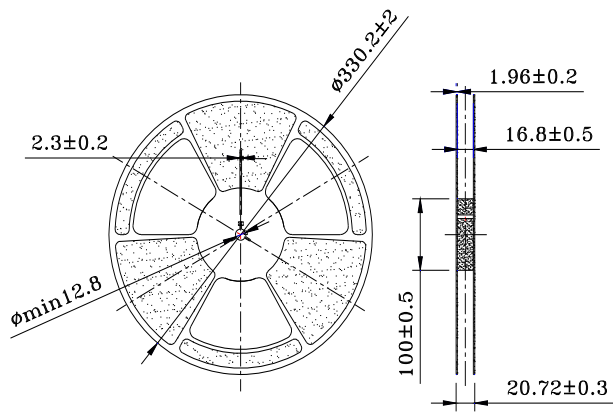
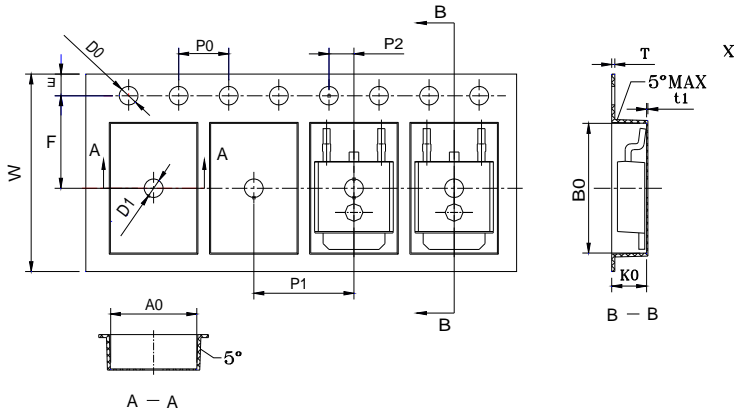
PACKAGE MECHANICAL DATA



Ref.	Dimensions		
	Millimeters		
	Min.	Typ.	Max.
A	2.200	/	2.400
A1	/	/	0.127
B	0.635	/	0.770
C	0.460	/	0.580
D	5.100	/	5.460
D1	6.000	/	6.200
D2	4.830REF		
G	12.000	12.100	12.200
L	0.600	/	1.000

TO-252

DELIVERY MODE



Ref.	Dimensions		
	Millimeters		
	Min.	Typ.	Max.
W	15.90	16.00	16.10
E	1.65	1.75	1.85
F	7.40	7.50	7.60
D0	1.50	1.55	1.60
D1	1.50	/	/
P0	3.90	4.00	4.10
P1	7.90	8.00	8.10
P2	1.90	2.00	2.10
10P0	39.8	40.00	40.20
A0	6.80	6.90	7.00
B0	10.40	10.50	10.60
K0	2.60	2.70	2.80
T	0.25	0.30	0.35
t1	0.10	/	/

PACKAGE	OUTLINE	REEL (PCS)	PER CARTON (PCS)
TO-252	TAPING	2,500	5,000

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

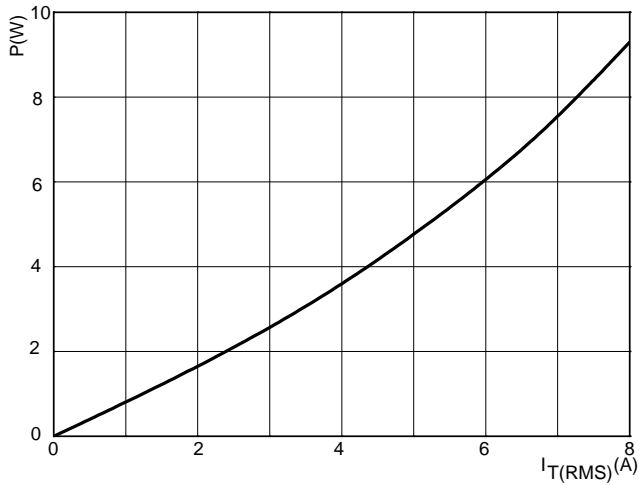


FIG.2: RMS on-state current versus case temperature (full cycle)

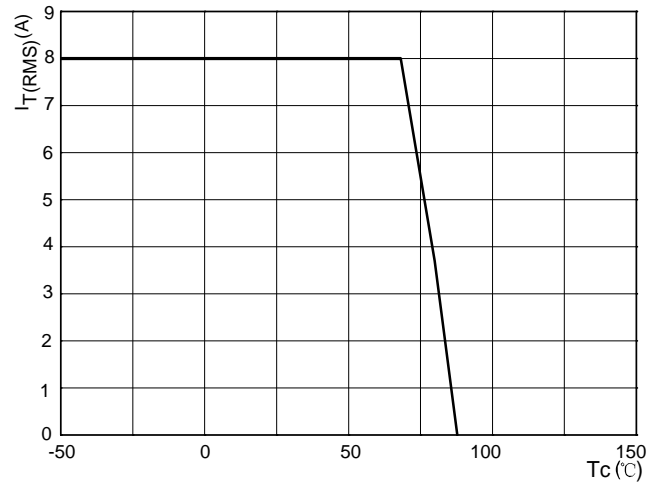


FIG.3: Surge peak on-state current versus number of cycles

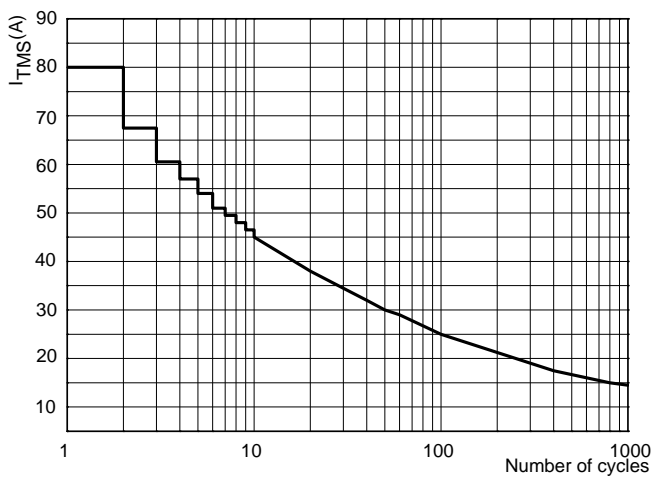


FIG.4: On-state characteristics (maximum values)

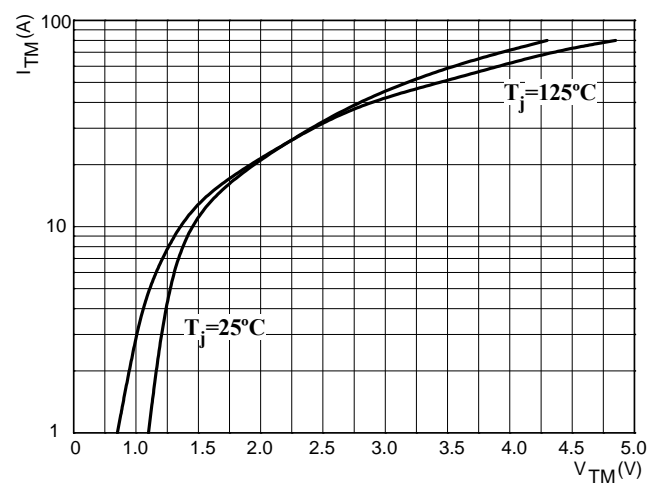


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10ms$

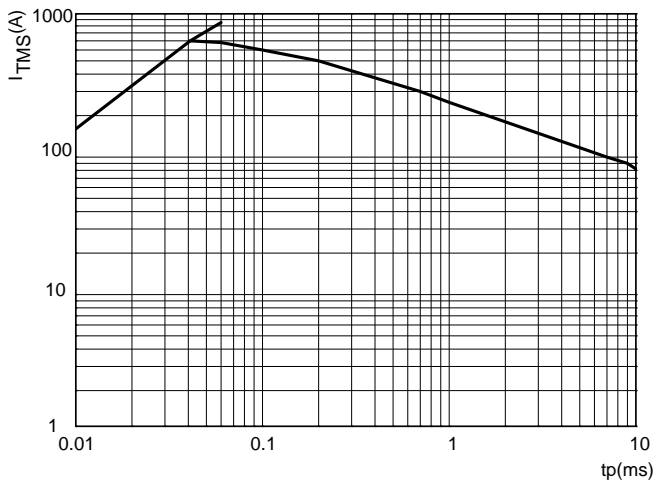
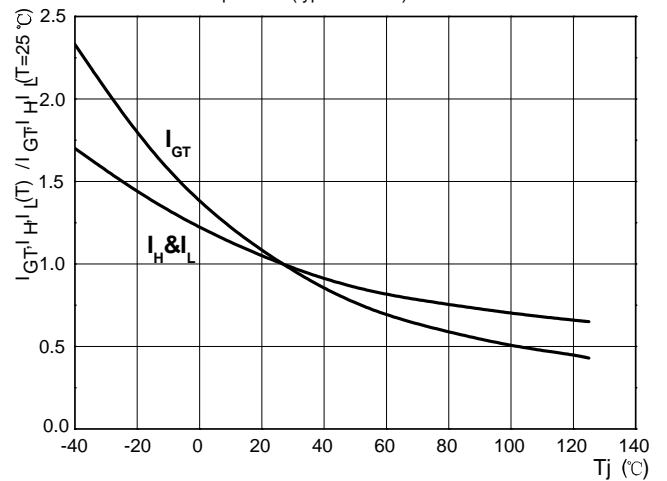


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



单击下面可查看定价，库存，交付和生命周期等信息

[>>ZG\(中鑫半导体\)](#)